

ALTERNATIVE TO PTO/SB/08A/B
(Based on PTO 03-08 version)

Substitute for form 1449/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Application Number	10/537,804
		Filing Date	June 7, 2005
		First Named Inventor	Robert DWILINSKI
		Art Unit	1792
		Examiner Name	F.C. Hiteshew
Sheet	1	of	5
		Attorney Docket Number	204552035400

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Examiner Initials*	Cite No.	Document Number Number-Kind Code* (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Examiner Signature	/Felisa Hiteshew/	Date Considered	10/07/2008
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